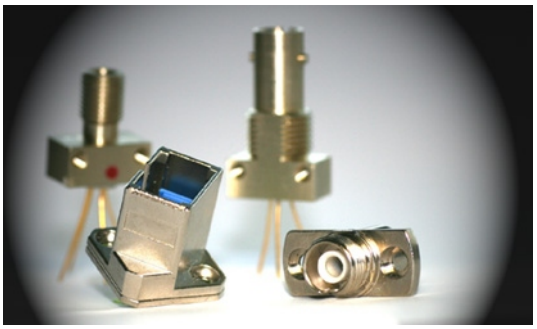
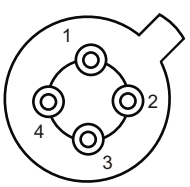
PIN-TIA Receiver 2.5 Gbps with AGC



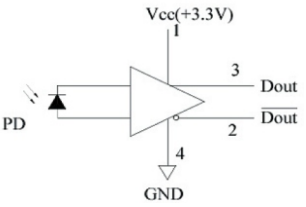
Features of Diode

- InGaAs/InP PIN Photodiode with Transimpedance Amplifier
- High sensitivity with AGC
- Differential ended output
- Single 3.3 V operation
- -40 to 85 °C operating temperature
- Integrated 4-pin TO-46 ball lens cap package
- 2.5 Gbps SDH/SONET/ATM receiver application

PINOUT



Bottom view



Absolute maximum ratings

Parameter	Min.	Max.
Storage temperature	-40 °C	85 °C
Operating temperature	-40 °C	85 °C
Supply voltage		3.8 V

Number	Function
1	V_{CC}
2	$\overline{D_{out}}$
3	D_{out}
4	GND

Electrical-optical characteristics

Parameter Laser Diode	Test Condition	Min.	Typ.	Max.
Power supply	T_C= 25 °C	3.0 V	3.3 V	3.6 V
Differential output voltage	T_C= 25 °C		0.6 V	
Supply current	T_C= 25 °C		26 mA	38 mA
Detection range	T_C= 25 °C	1100 nm	1310 nm	1650 nm
Gain @ 10 Mbps Differential	= 1310 nm		27 V/mW	
Bandwidth	T_C= 25 °C	1.7 GHz	1.9 GHz	
Saturation power	= 1310 nm	-3 dBm	0 dBm	
Sensitivity	BER= 10^{-10}@2.5 Gbps, PRBS 2^{23}-1		-21 dBm	-18 dBm
Output resistance	T_C= 25 °C	40	53	65
Possible receptacle (**type A**)	ST1, ST2, ST4, P2, LC, SC, Fc1, FC2, Fiberdip, SMA1, SMA2			

Compliant with RoHS-requirements (2002/95/EG vom 27.01.2003)

Note: The above product specifications are subject to change without notice.